



鑫沃科技
XIN WO TECHNOLOGY



SI2309

P Channel Advanced Power MOSFET
SOT23/-60V/-2A

深圳东为电子科技有限公司
DONGWEI ELECTRONIC TECHNOLOGY CO., LTD

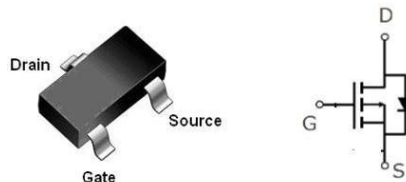
Features

- Low $R_{DS(on)}$ @ $V_{GS} = -10V$
- -5V Logic Level Control
- P Channel SOT23 Package
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
-60V	145mΩ @ 10V	-2A
	180mΩ @ 4.5V	

Applications

- Load Switch
- Switching Circuits
- High Speed line Driver

**Order Information****SOT23**

Product	Package	Marking	Packing	Min Unit Quantity
SI2309	SOT23	N9L8K	3000PCS/Reel	3000PCS

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit	
Common Ratings (TA=25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage	±20	V	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	-60	V	
T _J	Maximum Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-50 to 150	°C	
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested①	TA=25°C	-6	A
I _D	Continuous Drain Current	TA=25°C	-2	A
		TA=70°C	-1.4	
P _D	Maximum Power Dissipation	TA=25°C	1	W
		TA=70°C	0.8	
R _{θJA}	Thermal Resistance Junction-Ambient		125	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =-60V, V _{GS} =0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =-60V, V _{GS} =0V	--	--	-100	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.1	-1.8	-2.1	V
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-10V, I _D =-2A	--	145	190	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-4.5V, I _D =-1A	--	180	280	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz	--	310	--	pF
C _{oss}	Output Capacitance		--	22	--	pF
C _{rss}	Reverse Transfer Capacitance		--	15	--	pF
Q _g	Total Gate Charge		--	5.4	--	nC
Q _{gs}	Gate Source Charge		--	1.1	--	nC
Q _{gd}	Gate Drain Charge		--	1.6	--	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =-30V, I _D =-2A, R _G =3.3Ω, V _{GS} =-10V	--	41	--	ns
t _r	Turn on Rise Time		--	22	--	ns
t _{d(off)}	Turn Off Delay Time		-	25	--	ns
t _f	Turn Off Fall Time		--	32	--	ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _A =25°C	--	--	-1.4	A
V _{SD}	Forward on voltage②	T _J =25°C, I _{SD} =-2A, V _{GS} =0V	--	-0.84	-1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

② Pulse test ; Pulse width≤300μs, duty cycle≤2%.

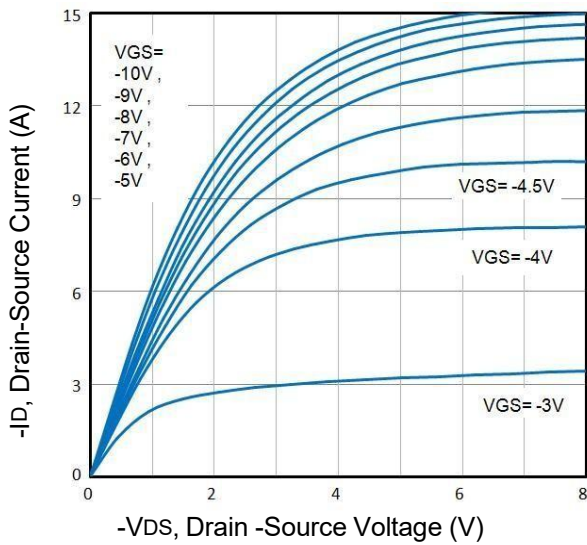


Fig1. Typical Output Characteristics

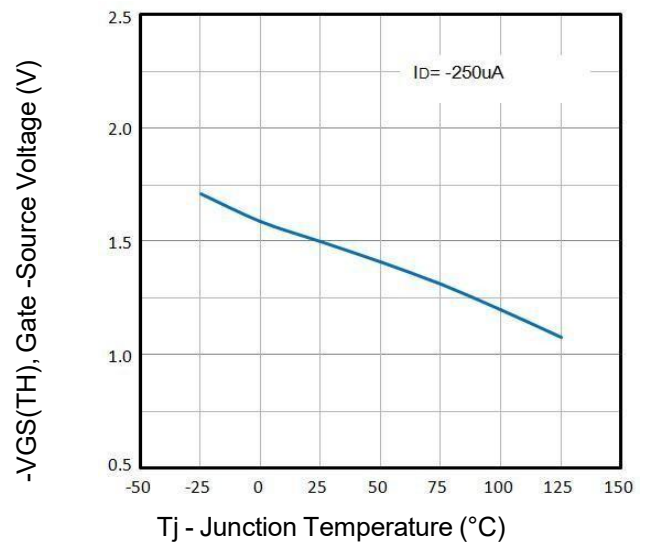


Fig2. Normalized Threshold Voltage Vs. Temperature

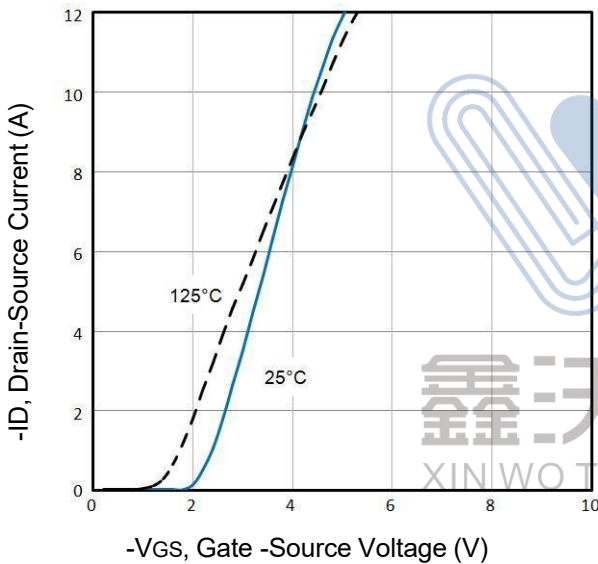


Fig3. Typical Transfer Characteristics

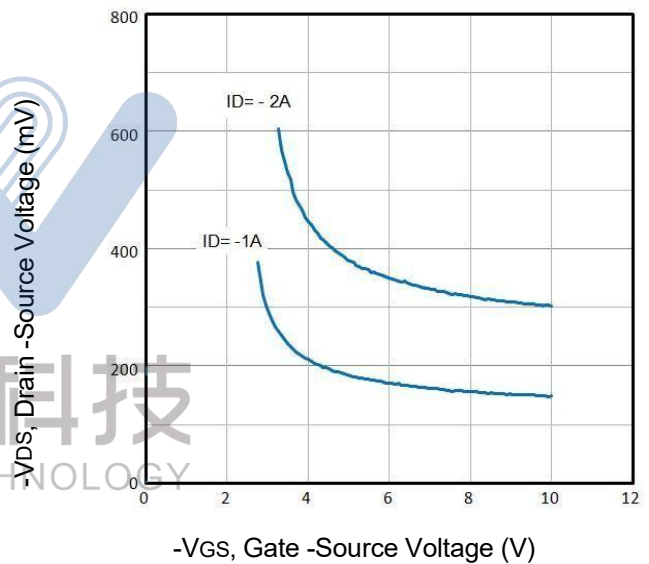


Fig4. Drain-Source Voltage vs Gate-Source Voltage

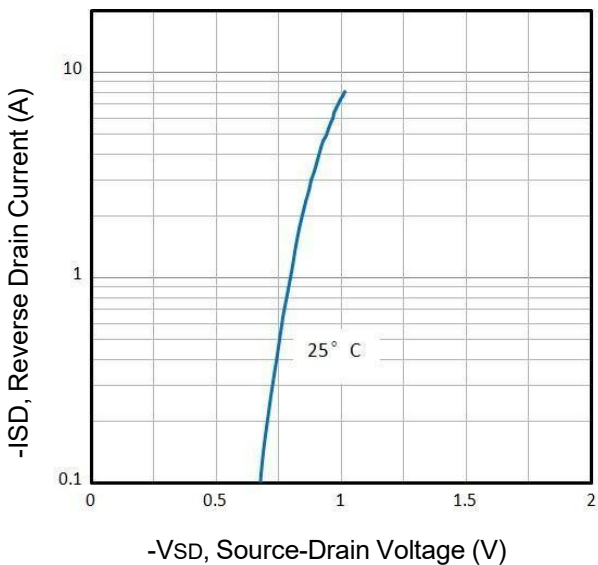


Fig5. Typical Source-Drain Diode Forward Voltage

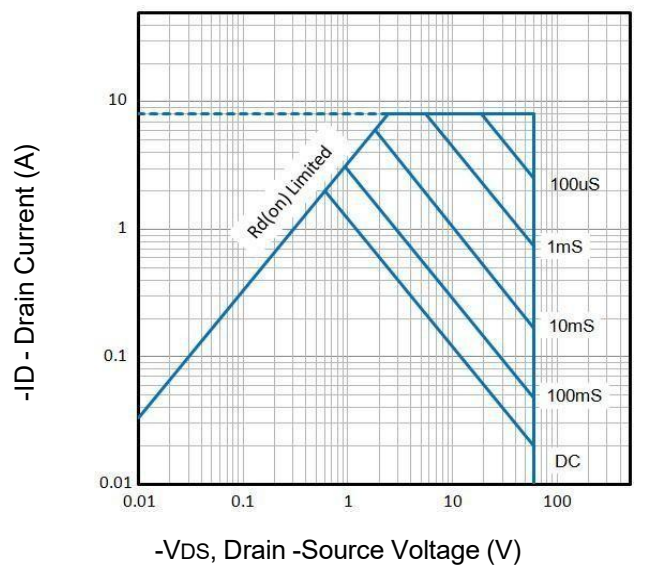


Fig6. Maximum Safe Operating Area

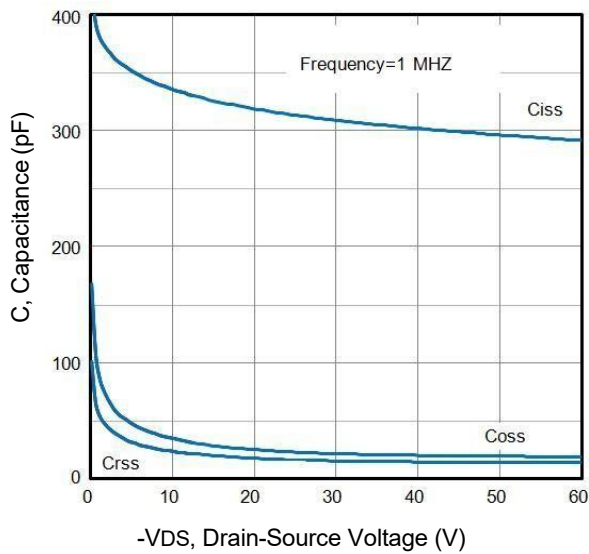


Fig7. Typical Capacitance Vs. Drain-Source Voltage

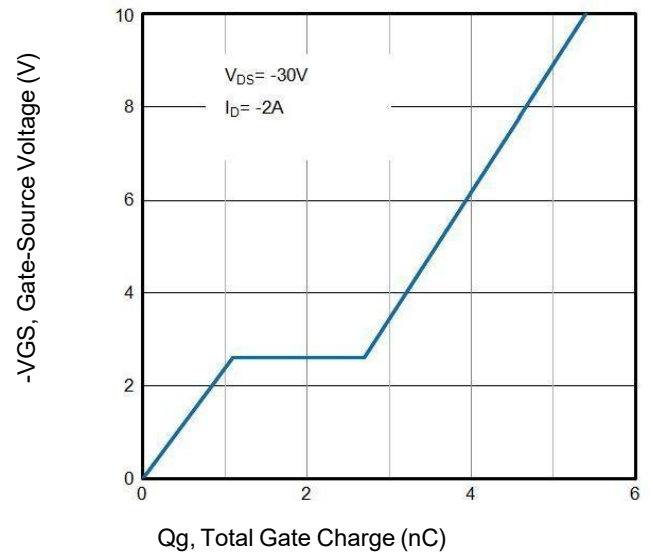


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

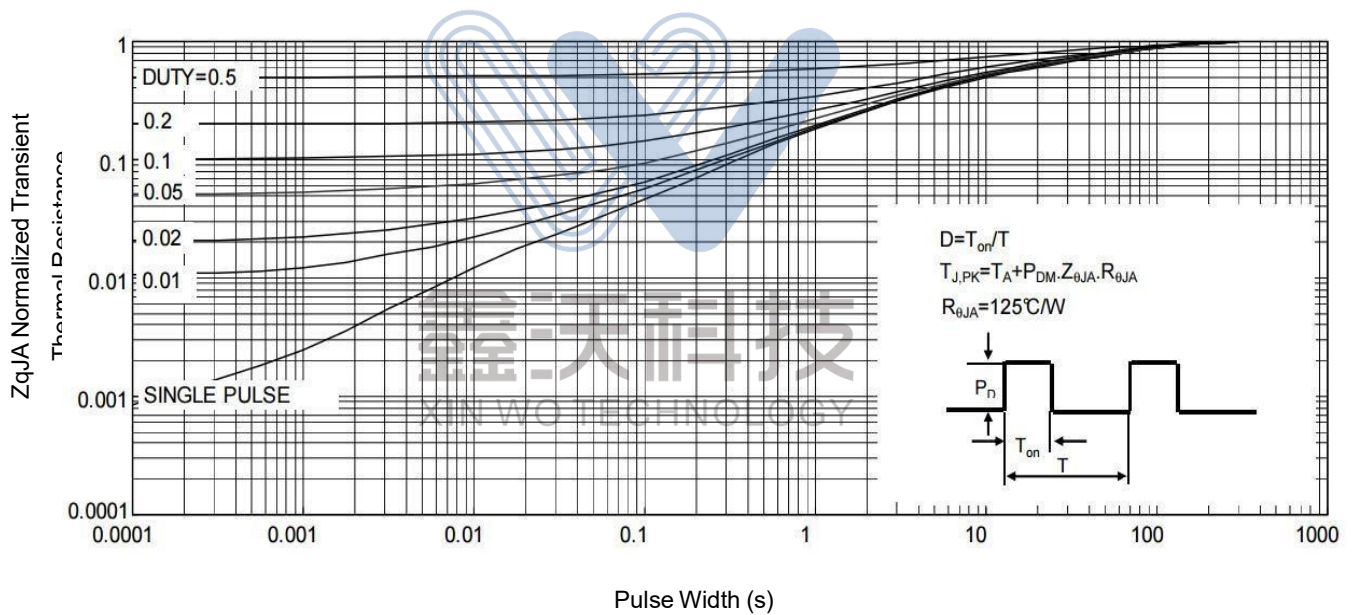


Fig9. Normalized Maximum Transient Thermal Impedance

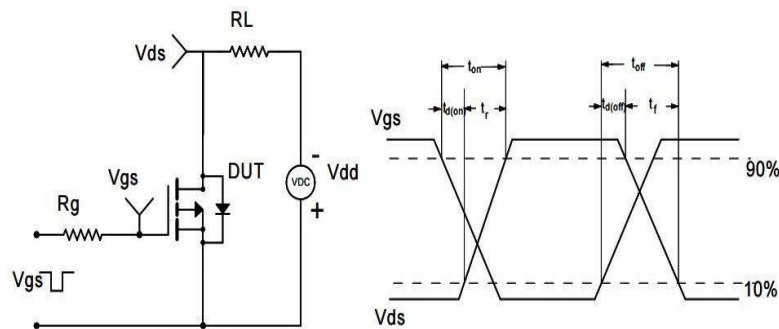
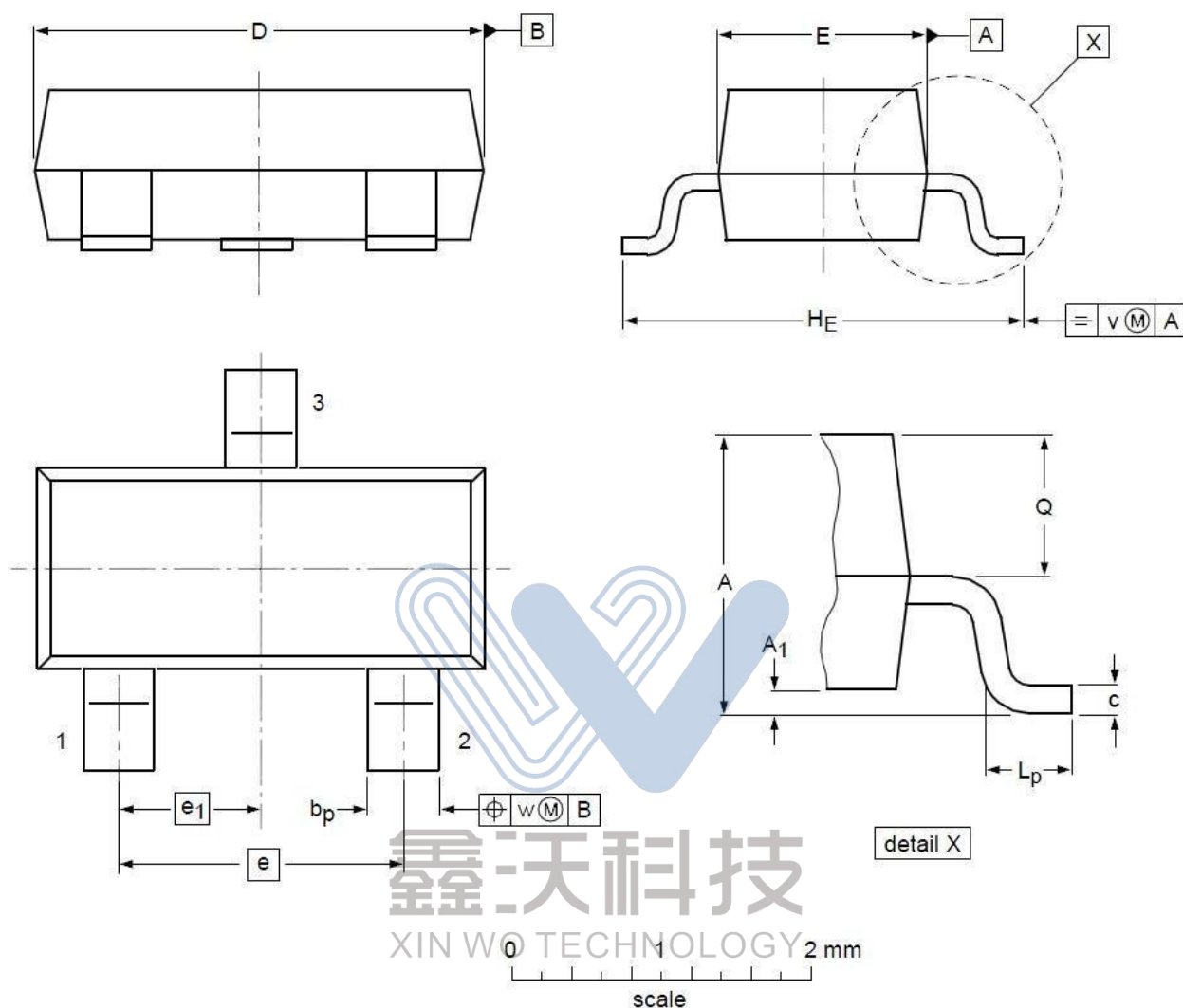


Fig10. Switching Time Test Circuit and waveforms

Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				